

DESCRIPTION

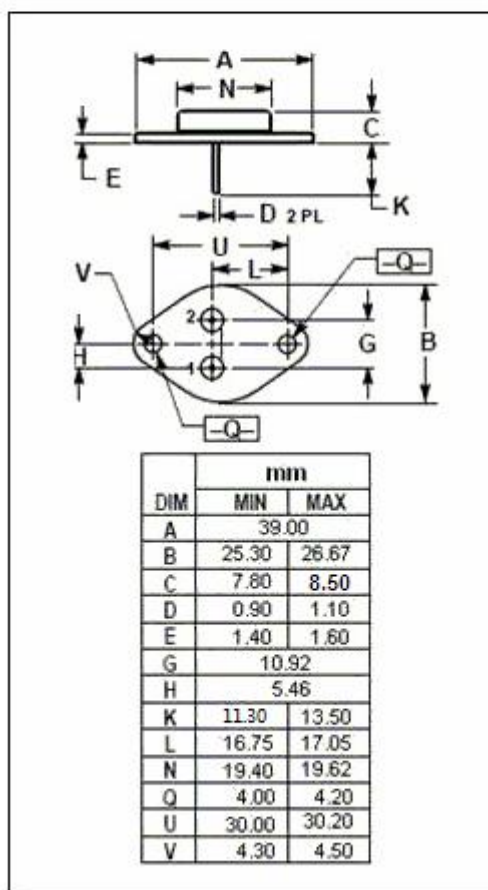
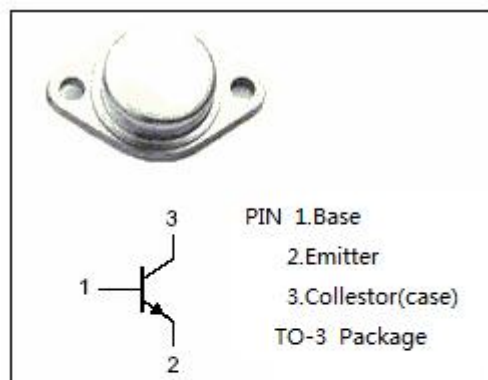
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 200V$ (Min)
- High Power Dissipation
- Complement to Type 2SB600

APPLICATIONS

- Designed for high speed, high current and high power applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	10	A
P_C	Collector Power Dissipation @ $T_c=25^\circ C$	200	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~200	$^\circ C$



SPTECH Silicon NPN Power Transistor**2SD555****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 1A			3.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10A; I _B = 1A			3.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 200V; I _E = 0			0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 3V; I _C = 0			0.1	mA
h _{FE-1}	DC Current Gain	I _C = 50mA; V _{CE} = 5V	20	50		
h _{FE-2}	DC Current Gain	I _C = 2A; V _{CE} = 5V	40	70	200	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz		300		pF
f _T	Current-Gain—Bandwidth Product	I _C = 1A; V _{CE} = 10V		7		MHz

◆ **h_{FE-2} Classifications**

S	R	Q
40-80	60-120	100-200